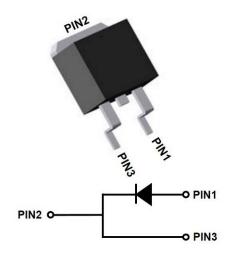




# Silicon Carbide Schottky Diode

$V_{RRM}$	650 V
I <sub>F (135°C)</sub>	9 A
Q <sub>C</sub>	21.5 nC



#### **Features**

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

#### **Typical Applications**

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

#### **Mechanical Data**

• Package: TO-263

• Terminals: Tin plated leads

• Polarity: As marked

### ■Maximum Ratings (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Device marking code			D106506BYG5
Reverse voltage (Repetitive peak) @ Tj=25°C	$V_{RRM}$	V	650
Reverse voltage (Surge peak) @ T <sub>j</sub> =25°C	$V_{RSM}$	٧	650
Reverse voltage (DC) @ T <sub>i</sub> =25°C	V <sub>DC</sub>	V	650
Continuous forward current @ T <sub>C</sub> =25°C			19
Continuous forward current @ T <sub>C</sub> =135°C	l <sub>F</sub>	А	9
Continuous forward current @ T <sub>C</sub> =155°C			6
Non-repetitive peak forward surge current @ T <sub>C</sub> =25°C, tp=10ms, Half Sine Wave	I <sub>FSM</sub>	А	65
Power Dissipation@ T <sub>C</sub> =25°C	0		75
Power Dissipation@ T <sub>C</sub> =110°C	P <sub>TOT</sub>	W	32
i²t Value@ T <sub>C</sub> =25°C ,tp=10ms	∫ i²dt	A <sup>2</sup> S	21
Operating junction and Storage temperature range	$T_j$ , $T_{stg}$	°C	-55 to +175

## YJD106506BYG5

## **■Electrical Characteristics** (T<sub>a</sub>=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.
Forward voltage drop	V <sub>F</sub>	>	I <sub>F</sub> =6A, T <sub>j</sub> =25°C	1.30	1.55
			I <sub>F</sub> =6A, T <sub>j</sub> =175°C	1.65	-
Reverse leakage	I <sub>R</sub>	μА	V <sub>R</sub> =650V, T <sub>j</sub> =25°C	0.5	25
			V <sub>R</sub> =650V, T <sub>j</sub> =175°C	36	-
Total capacitive charge	Qc	nC	$V_R$ =400V, $T_j$ =25°C, $QC$ = $\int_0^{VR}C(V)dV$	21.5	-
Total capacitance	С	pF	V <sub>R</sub> =0V, f=1MHZ	382	-
			V <sub>R</sub> =200V, f=1MHZ	41	-
			V <sub>R</sub> =400V, f=1MHZ	40	-
Capacitance stored energy	Ec	μJ	V <sub>R</sub> =400V	3.4	-

## ■Thermal Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Value
Thermal resistance	R <sub>eJ-C</sub>	°C W	2.0

## ■Typical Characteristics (Typical)

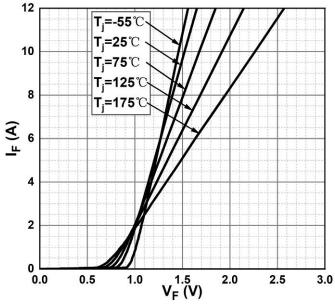


Figure 1. Forward Characteristics

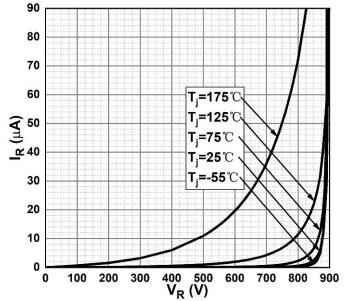
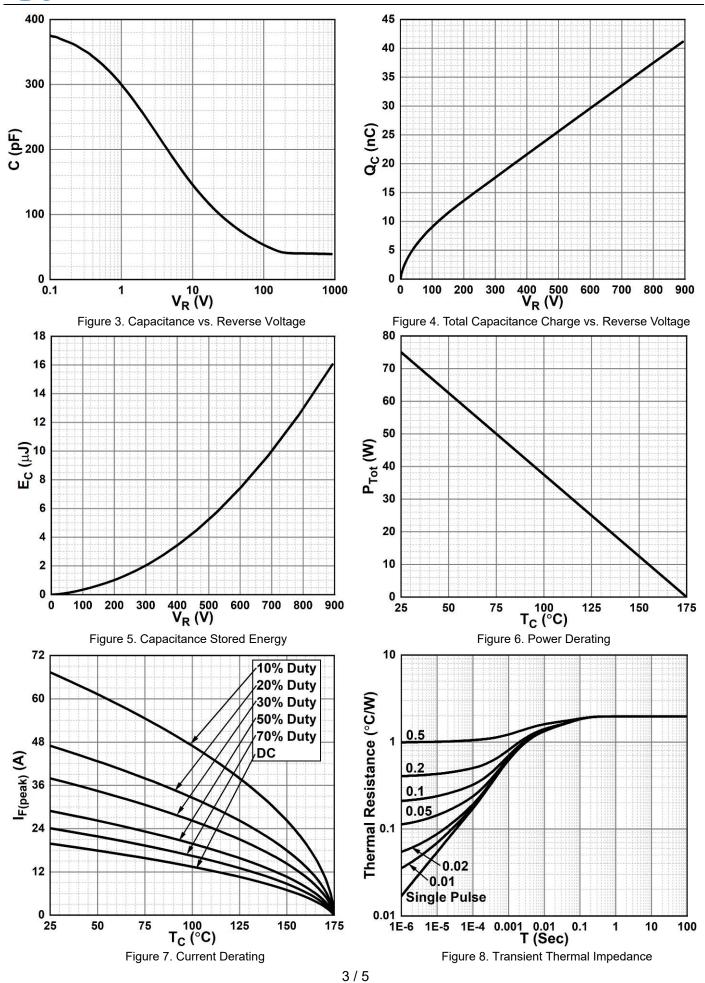


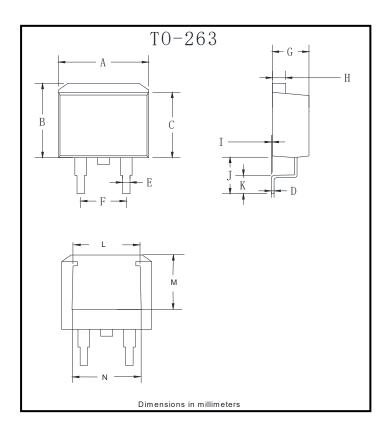
Figure 2. Reverse Characteristic

# YJD106506BYG5





## **■**Outline Dimensions



TO-263				
Dim	Min	Max		
Α	9.5	11.5		
В	9.7	10.5		
С	8.4	9.0		
D	0.28	0.64		
Е	0.68	0.94		
F	4.55	5.6		
G	4.04	5.10		
Н	1.14	1.4		
I	0	0.2		
J	4.9	6.05		
K	1.79	2.79		
L	7.3	7.9		
M	6.2	6.8		
N	7.6	8.2		



## YJD106506BYG5

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